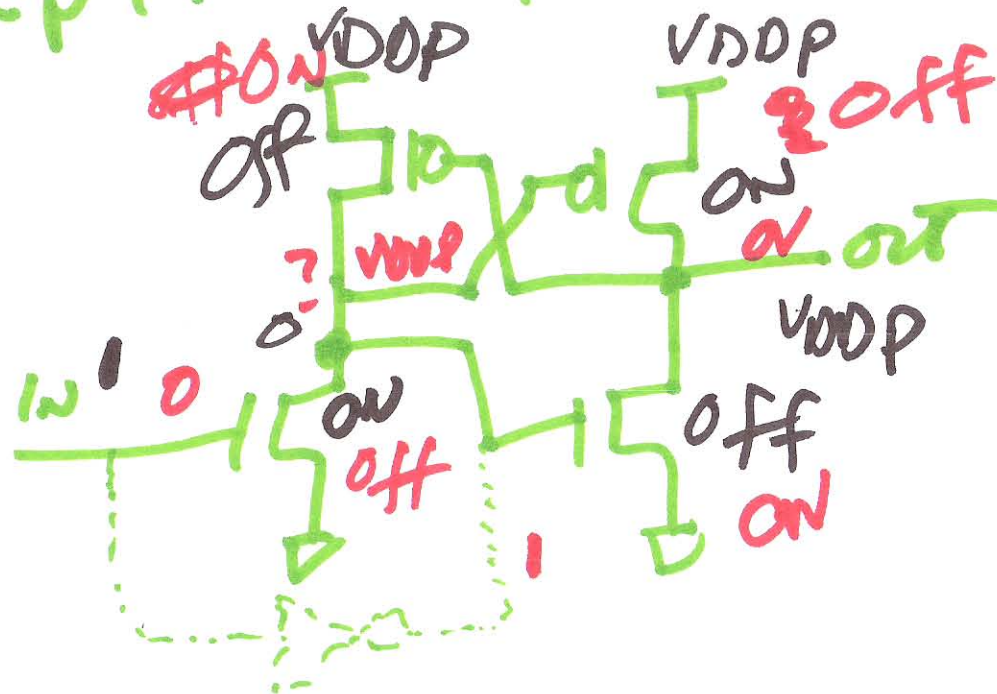


ECG 721

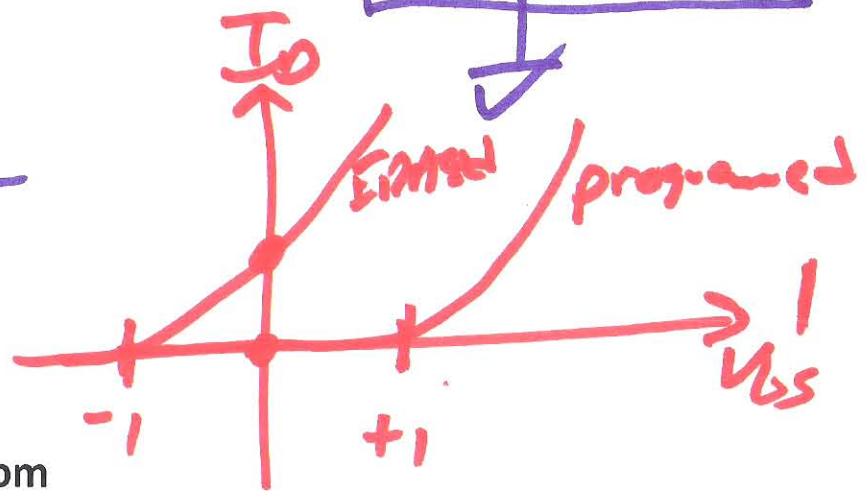
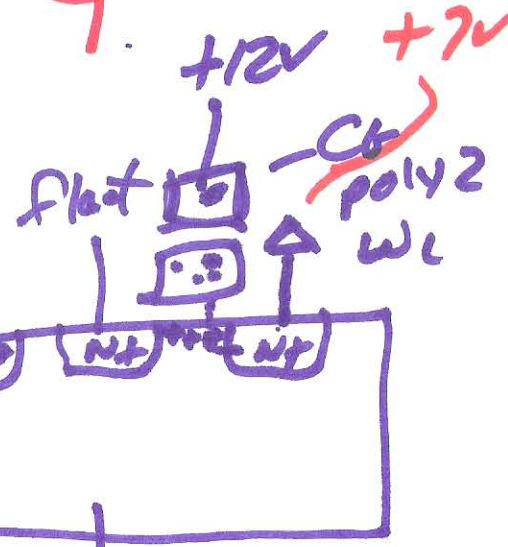
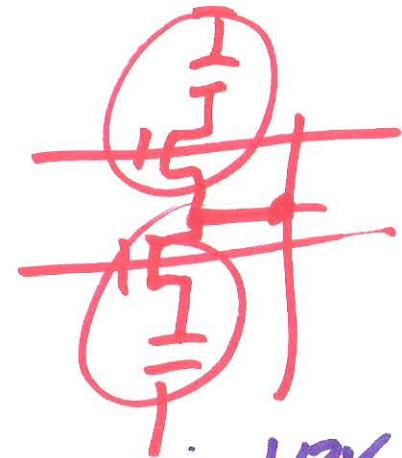
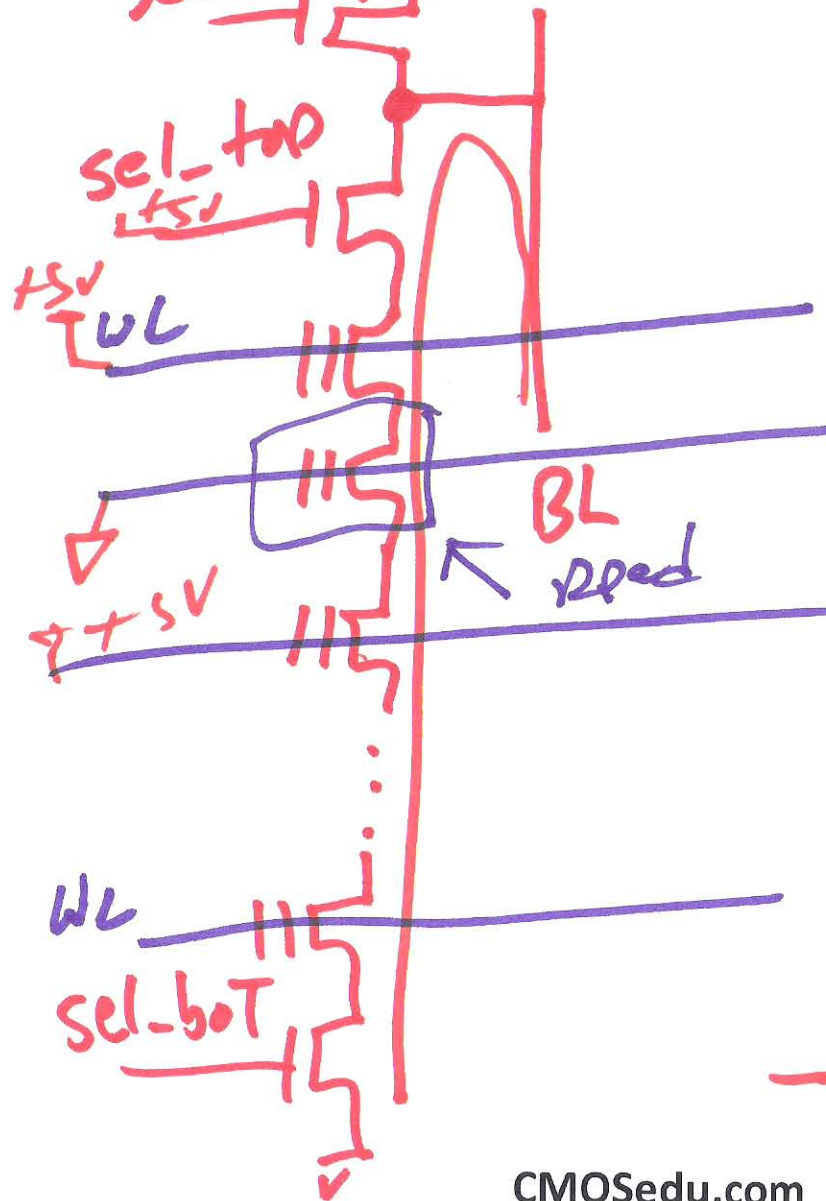
Memory Circuit Design

Sept. 21, 2015



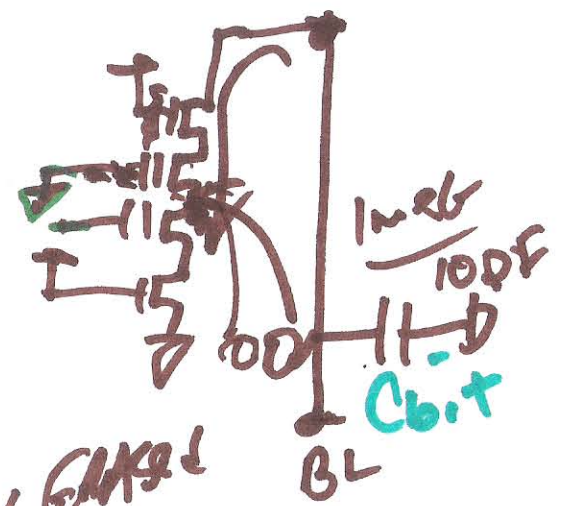
Ch. 16 Review

NAND Flash



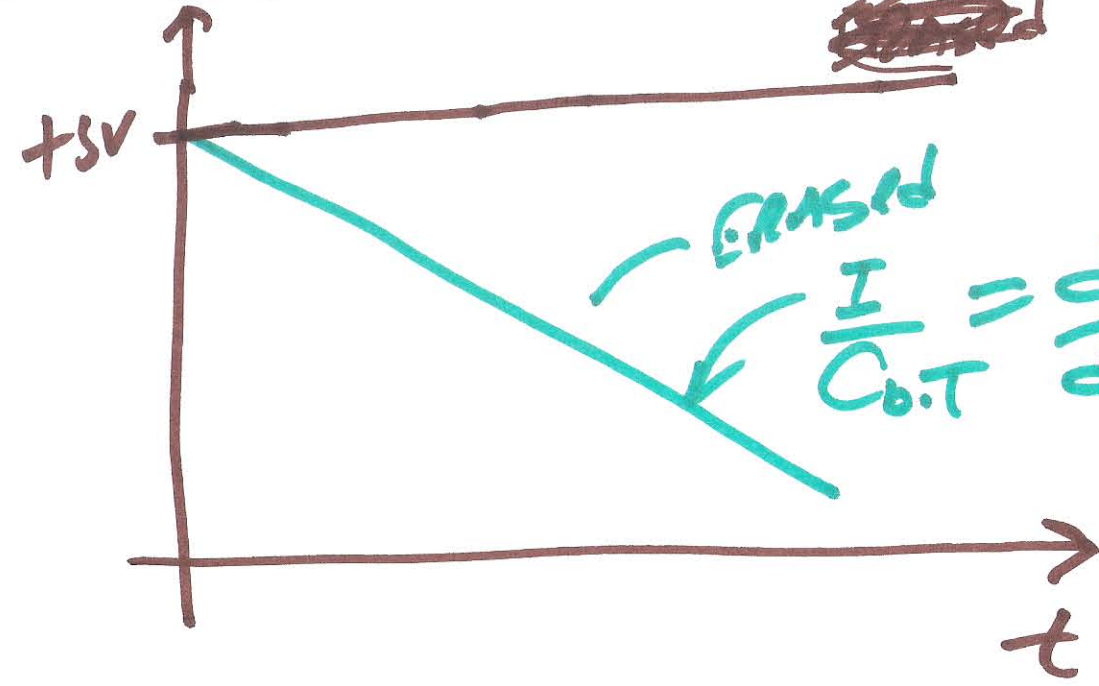
$$I = C \frac{dv}{dt}$$

$$RC = 104s$$



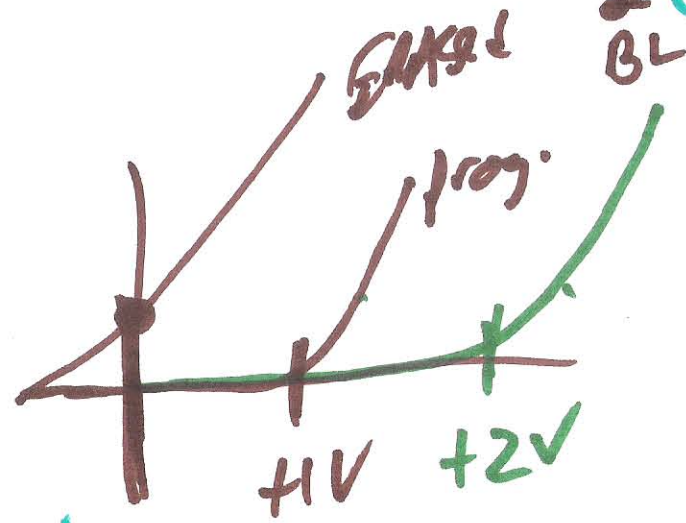
BL, voltage

Programmed
~~Erased~~



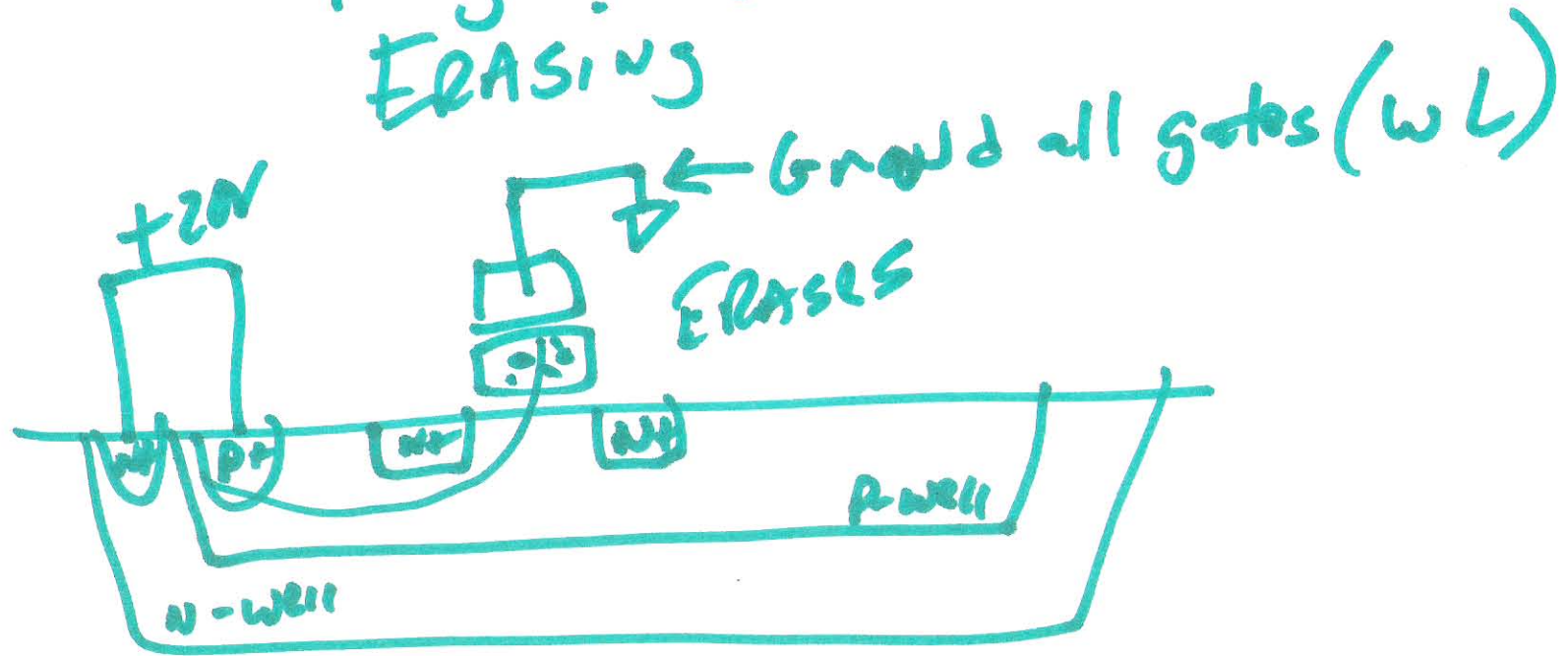
ERASED

$$\frac{I}{C_{b.T}} = \frac{dv}{dt}$$

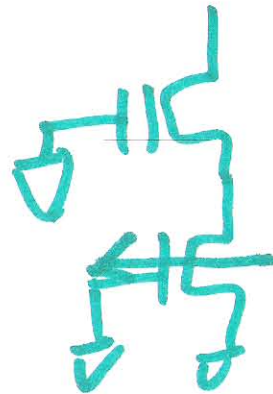


3)

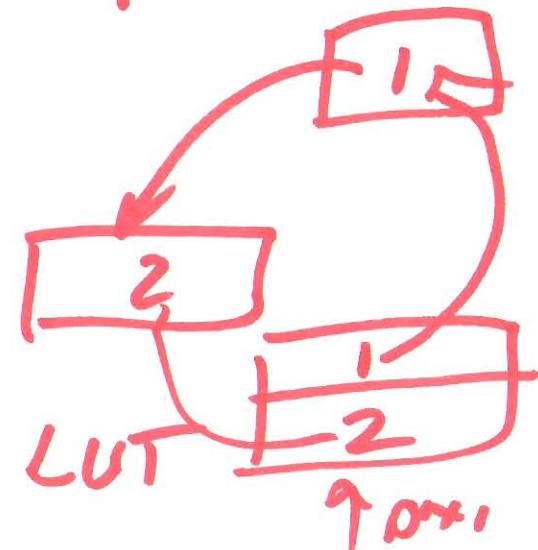
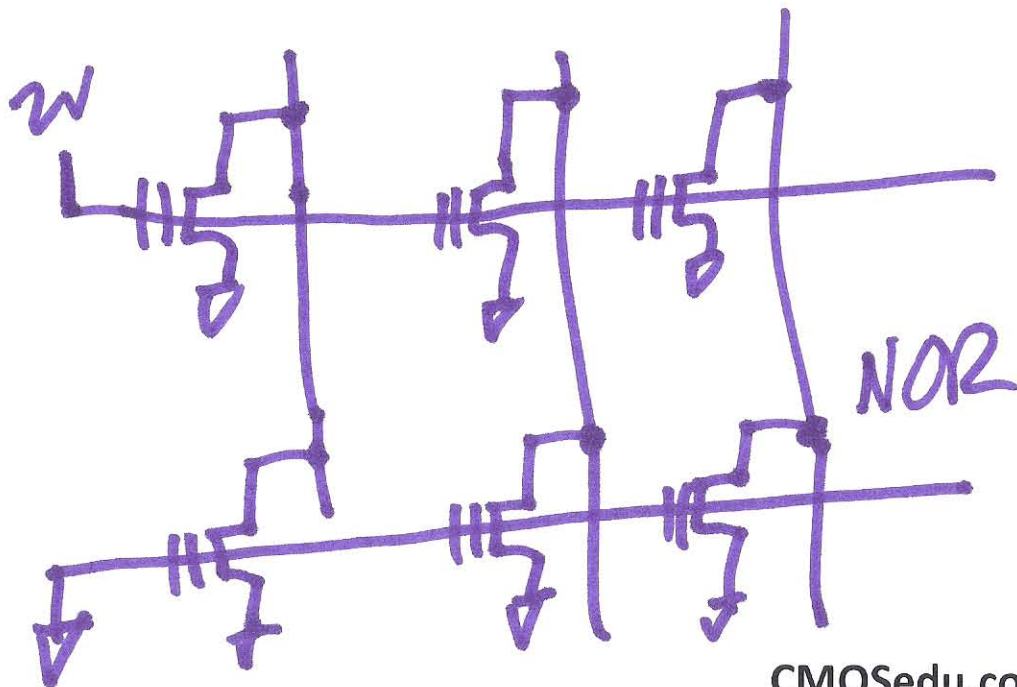
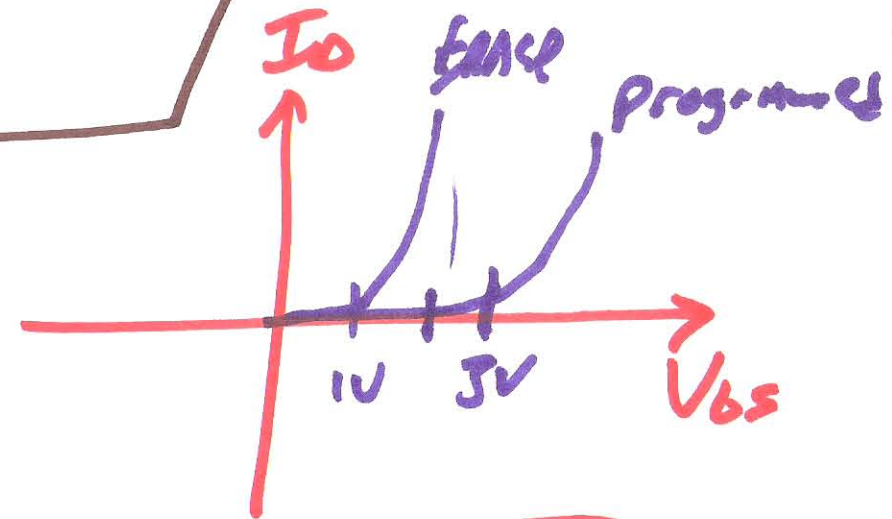
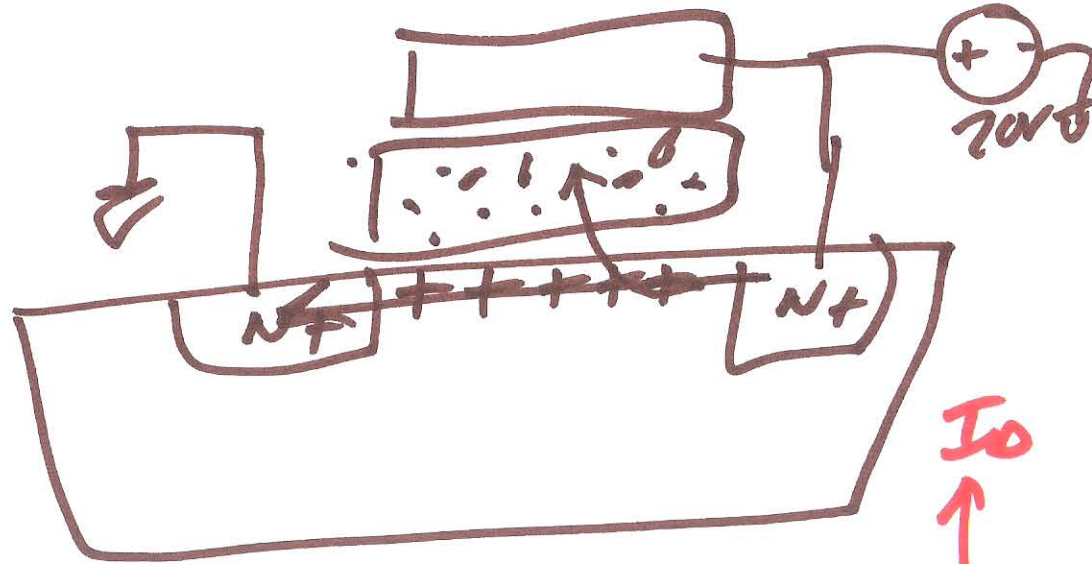
~~Programming~~ FNT ERASING



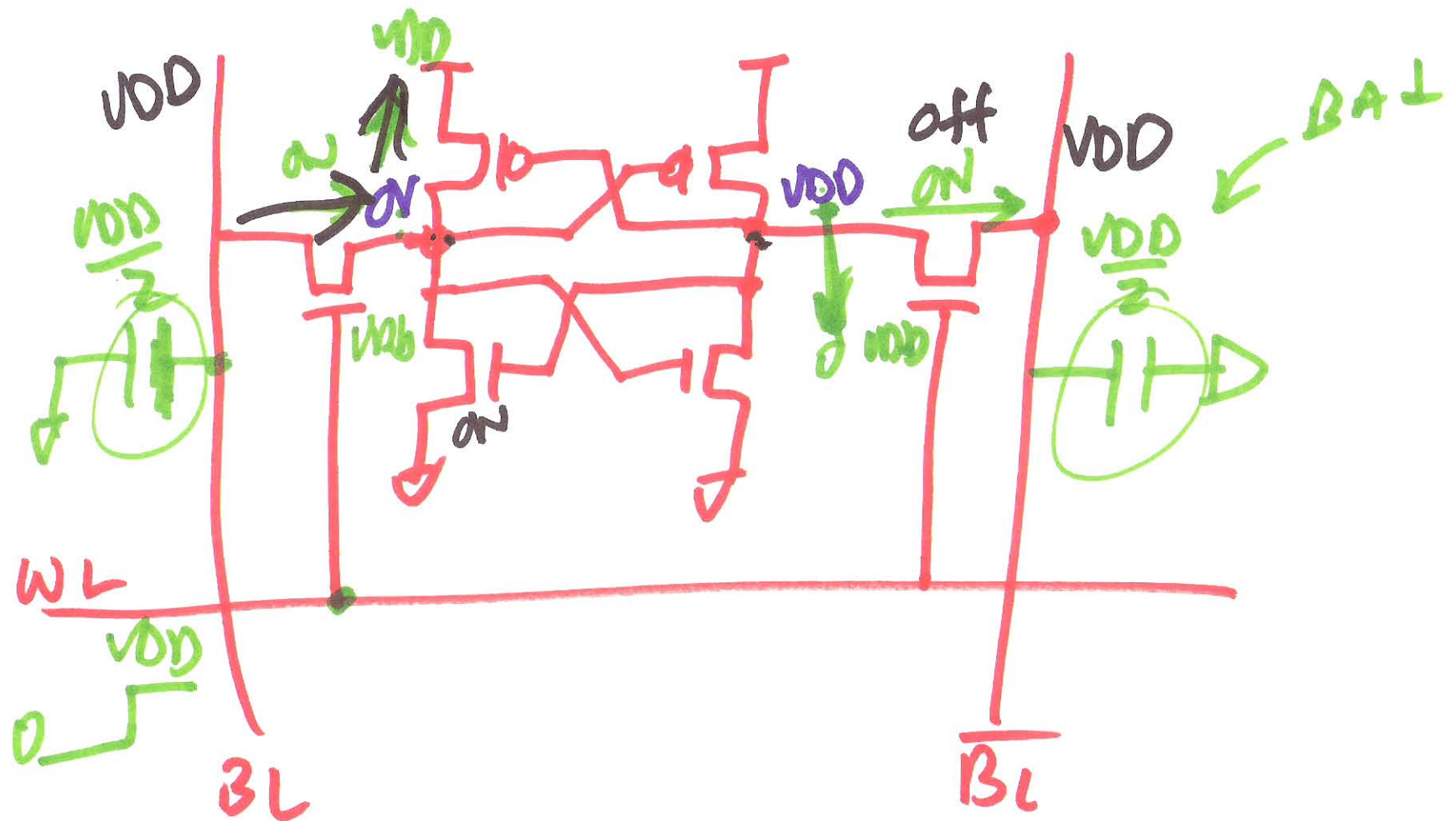
P-sub



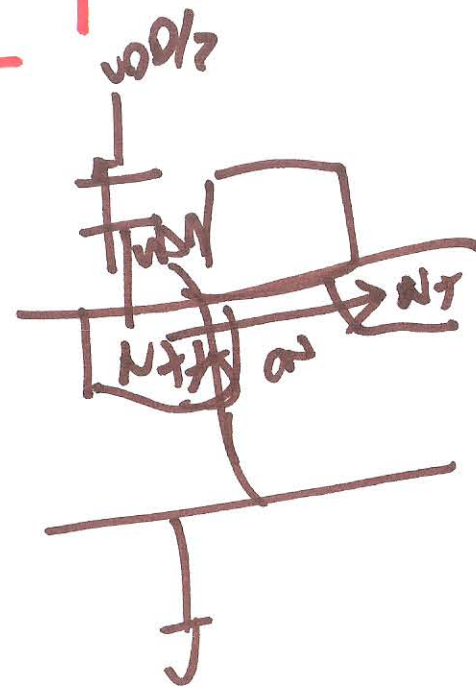
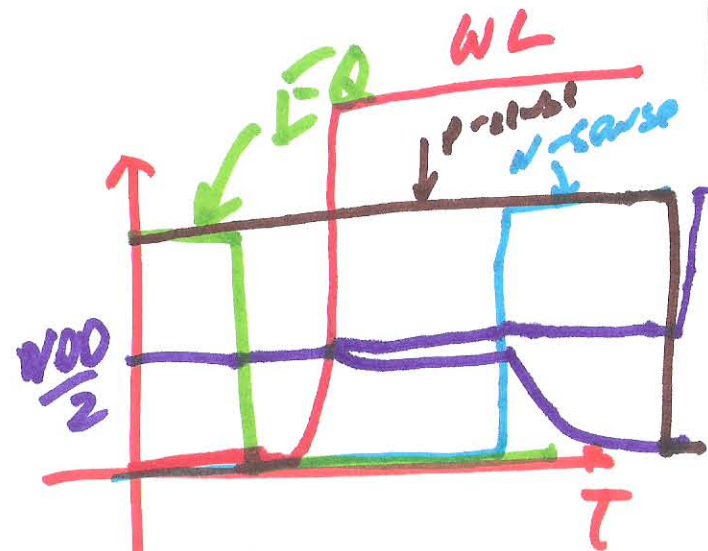
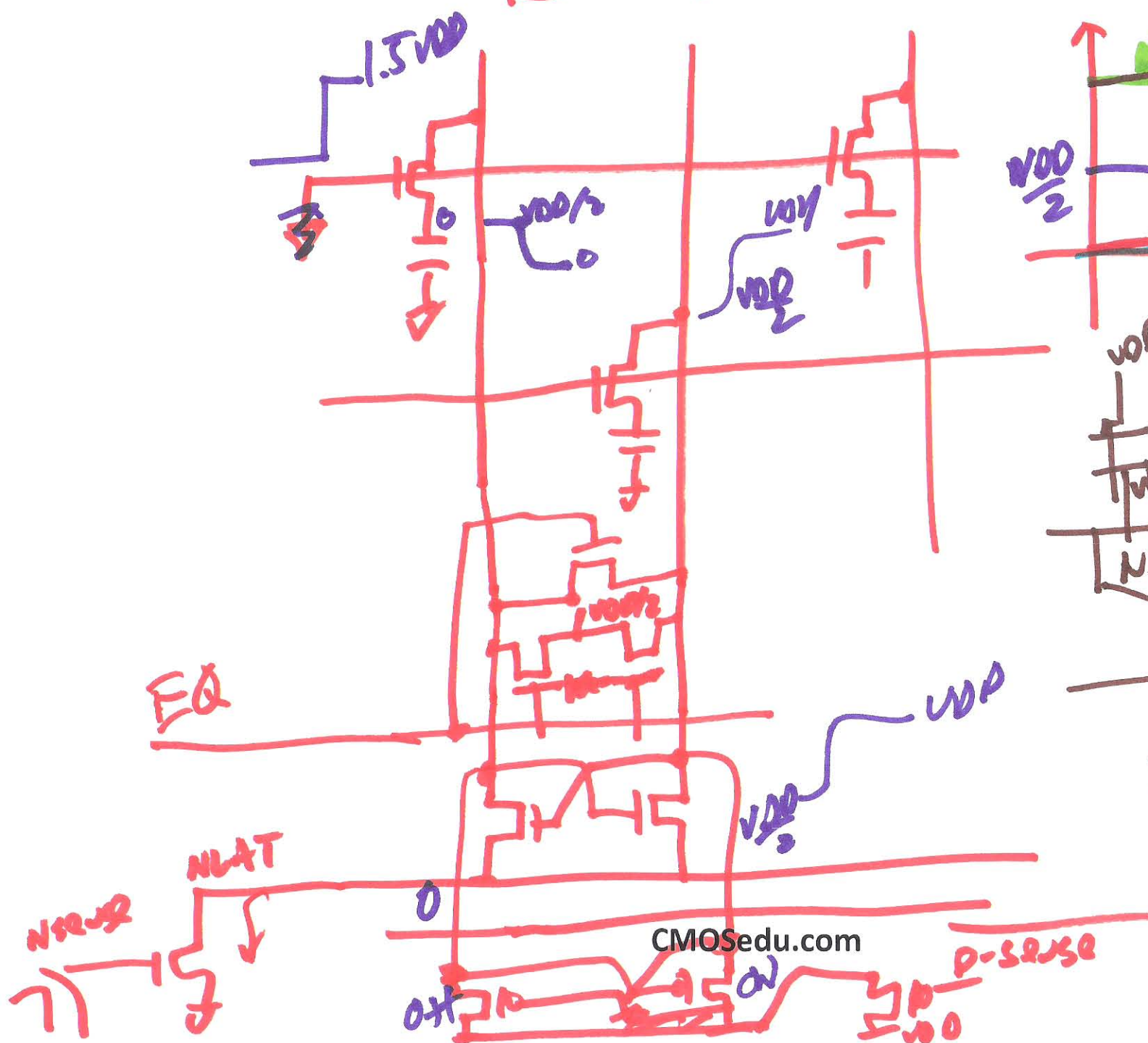
Channel Hot Electrons (CHE) Programming



6T-1SRAM



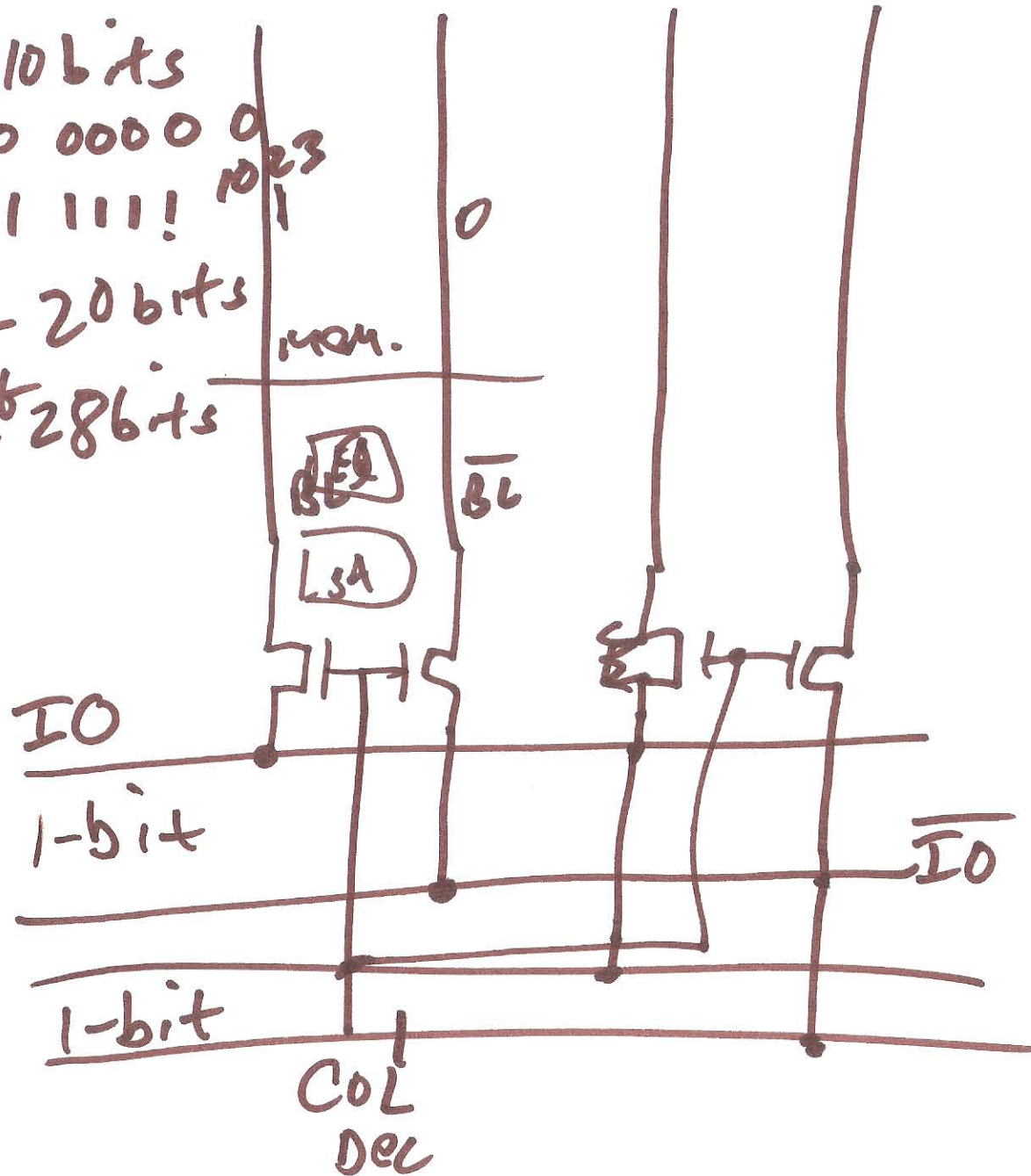
DRAM



1K - 10 bits
 000000 0000 0
 111111 1111 1023

1MEB - 20 bits

256 MEB - 28 bits



26b

256 M Words
 word = 8 bits

14-bits Row Add

14-bits Column Add

14-bits = 16 K

16 K Rows

16 K Cols

256K
 $S_{12} \equiv \begin{bmatrix} S_{12} & S_{12} \end{bmatrix}$

32 ARRAYS

~~512~~ ARRAYS

256

64 ARRAYS / 1M FL